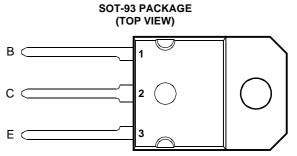
BOURNS®

- Designed for Complementary Use with BDW83, BDW83A, BDW83B, BDW83C and BDW83D
- 125 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3 V, 6 A



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDW84		-45		
	BDW84A		-60		
Collector-base voltage (I _E = 0)	BDW84B	V _{CBO}	-80	V	
	BDW84C		-100		
	BDW84D		-120		
	BDW84		-45		
Collector-emitter voltage (I _B = 0) (see Note 1)	BDW84A		-60		
	BDW84B	V_{CEO}	-80	V	
	BDW84C		-100		
	BDW84D		-120		
Emitter-base voltage		V_{EBO}	-5	V	
Continuous collector current		I _C	-15	Α	
Continuous base current		Ι _Β	-0.5	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	P _{tot}	125	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)	P _{tot}	3.5	W		
Unclamped inductive load energy (see Note 4)	½Ll _C ²	100	mJ		
Operating junction temperature range	T _j	-65 to +150	ç		
Operating temperature range	T _{stg}	-65 to +150	ç		
Operating free-air temperature range	T _A -65 to +150		°C		

NOTES: 1. These values apply when the base-emitter diode is open circuited.

- 2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER			TEST CONDITIONS				TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA	I _B = 0	(see Note 5)	BDW84 BDW84A BDW84B BDW84C BDW84D	-45 -60 -80 -100 -120			V
I _{CEO}	Collector-emitter cut-off current	V _{CE} = -30 V V _{CE} = -30 V V _{CE} = -40 V V _{CE} = -50 V V _{CE} = -60 V	$I_{B} = 0$		BDW84 BDW84A BDW84B BDW84C BDW84D			-1 -1 -1 -1	mA
Ісво	Collector cut-off current	$V_{CB} = -60 \text{ V}$ $V_{CB} = -80 \text{ V}$ $V_{CB} = -100 \text{ V}$ $V_{CB} = -120 \text{ V}$ $V_{CB} = -45 \text{ V}$ $V_{CB} = -60 \text{ V}$ $V_{CB} = -80 \text{ V}$	_	$T_{C} = 150^{\circ}\text{C}$	BDW84 BDW84B BDW84C BDW84D BDW84 BDW84A BDW84A BDW84A BDW84C BDW84C			-0.5 -0.5 -0.5 -0.5 -0.5 -5 -5 -5 -5	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0					-2	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = -3 V$ $V_{CE} = -3 V$	$I_{C} = -6 \text{ A}$ $I_{C} = -15 \text{ A}$	(see Notes 5 and 6)		750 100		20000	
V _{BE(on)}	Base-emitter voltage	V _{CE} = -3 V	$I_C = -6 A$	(see Notes 5 and 6)				-2.5	٧
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$ $I_B = -150 \text{ mA}$	$I_{C} = -6 \text{ A}$ $I_{C} = -15 \text{ A}$	(see Notes 5 and 6)				-2.5 -4	٧
V _{EC}	Parallel diode forward voltage	I _E = -15 A	I _B = 0					-3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

	PARAMETER			MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = -10 A	$I_{B(on)} = -40 \text{ mA}$	$I_{B(off)} = 40 \text{ mA}$		0.9		μs
t _{off}	Turn-off time	$V_{BE(off)} = 4.2 V$	$R_L = 3 \Omega$	t_p = 20 μ s, dc \leq 2%		7		μs

 $[\]begin{tabular}{ll} \uparrow Voltage and current values shown are nominal; exact values vary slightly with transistor parameters. \end{tabular}$

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN vs **COLLECTOR CURRENT** 10000 -40°C 25°C = 100°C h_{FE} - Typical DC Current Gain 1000 $V_{CE} = -3 V$ = 300 μs, duty cycle < 2% 100 -0-5 -1-0 -20 I_c - Collector Current - A

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

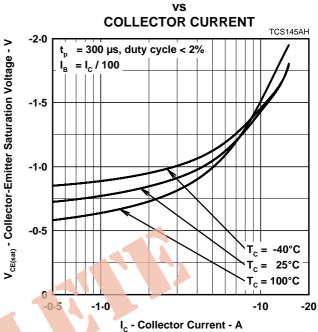


Figure 2.

BASE-EMITTER SATURATION VOLTAGE

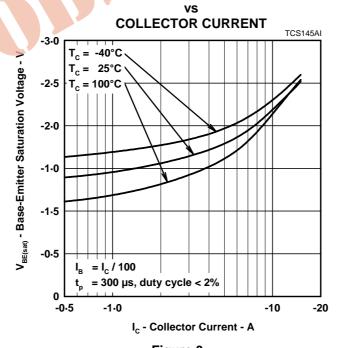
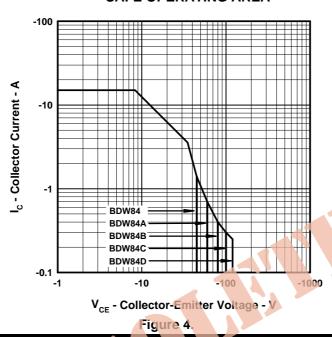


Figure 3.

PRODUCT INFORMATION

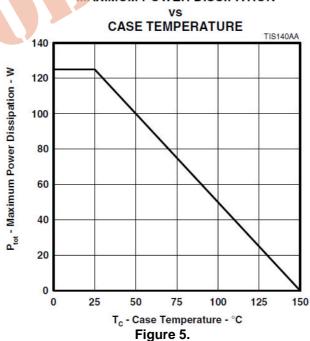
MAXIMUM SAFE OPERATING REGIONS

MAXIMUM FORWARD-BIAS SAFE OPERATING AREA



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION



PRODUCT INFORMATION

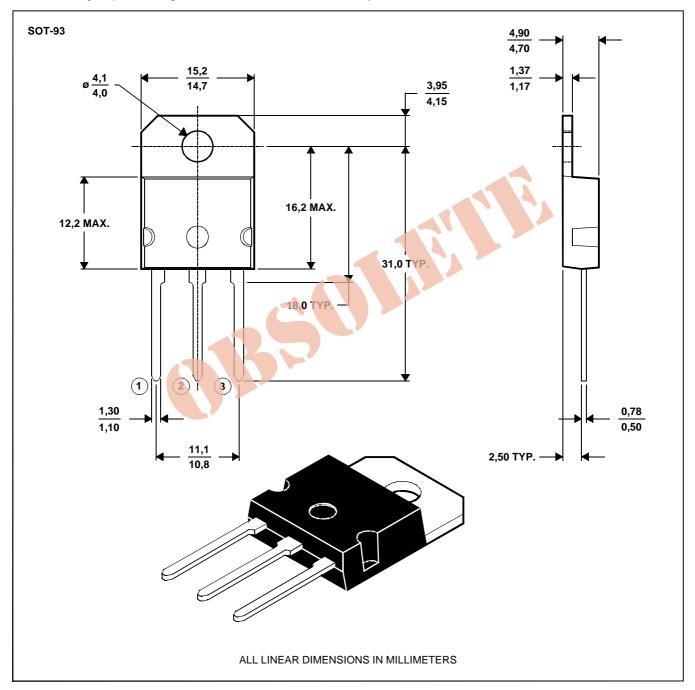


MECHANICAL DATA

SOT-93

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: The centre pin is in electrical contact with the mounting tab.

MDXXAW